

THE MECHANISM OF FORMATION OF
MICRODEFECTS IN DISLOCATIONLESS
MONOCRYSTALS OF SILICON

V. I. Talanin, I. E. Talanin, D. I. Levinson

Zaporizhzhya State Engineering Academy
(226, Lenina Prosp., Zaporizhzhya 69006, Ukraine)

S u m m a r y

The experimental results of researches of microdefects in dislocationless monocrystals of silicon obtained by the zone floating technique are represented. It is established that, near the front of crystallization, the concentrations of vacancies and interstitial atoms of silicon are identical. The disintegration of a solid solution of own dot defects occurs by two independent mechanisms - vacancy and interstitial ones. By the results of the conducted experiments, the mechanism of formation of microdefects is determined.